Transistors

## 2SB0621A

## Silicon PNP epitaxial planar type

For low-frequency driver amplification Complementary to 2SD0592A

#### ■ Features

- ullet Low collector-emitter saturation voltage  $V_{\text{CE(sat)}}$
- ullet High transition frequency  $f_T$

## $\blacksquare$ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter                             | Symbol           | Rating      | Unit |  |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V <sub>CBO</sub> | -60         | V    |  |
| Collector-emitter voltage (Base open) | V <sub>CEO</sub> | -50         | V    |  |
| Emitter-base voltage (Collector open) | V <sub>EBO</sub> | -5          | V    |  |
| Collector current                     | $I_{C}$          | -1          | A    |  |
| Peak collector current                | $I_{CP}$         | -1.5        | A    |  |
| Collector power dissipation           | P <sub>C</sub>   | 750         | mW   |  |
| Junction temperature                  | $T_{j}$          | 150         | °C   |  |
| Storage temperature                   | T <sub>stg</sub> | -55 to +150 | °C , |  |

#### Package

• Code

TO-92B-B1

- Pin Name
  - 1. Emitter
  - 2. Collector
  - 3. Base

### ■ Electrical Characteristics $T_a = 25$ °C±3°C

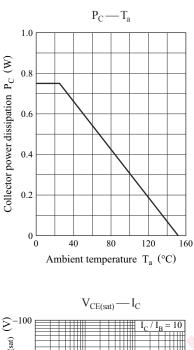
| Parameter   | Symbol               | Conditions   | Min | Тур             | Max  | Unit |
|---|----------------------|--|-----|-----------------|------|------|
| Collector-base voltage (Emitter open)                               | $V_{CBO}$            | $I_{\rm C} = -10 \mu\text{A}, I_{\rm E} = 0$                       | -60 |                 |      | V    |
| Collector-emitter voltage (Base open)                               | V <sub>CEO</sub>     | $I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$                         | -50 | Ö <sub>()</sub> |      | V    |
| Emitter-base voltage (Collector open)                               | $V_{\mathrm{EBO}}$   | $I_E = -10 \mu\text{A}, I_C = 0$                                   | -5  |                 |      | V    |
| Collector-base cutoff current (Emitter open)                        | $I_{CBO}$            | $V_{\rm CB} = -20 \text{ V}, I_{\rm E} = 0$                        | 50  |                 | -0.1 | μΑ   |
| Forward current transfer ratio                                      | h <sub>FE1</sub> *   | $V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$                  | 85  |                 | 340  |      |
|   | $h_{FE2}$            | $V_{CE} = -5 \text{ V}, I_{C} = -1 \text{ A}$                      | 50  |                 |      |      |
| Collector-emitter saturation voltage                                | V <sub>CE(sat)</sub> | $I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$                      |     | -0.2            | -0.4 | V    |
| Base-emitter saturation voltage                                     | V <sub>BE(sat)</sub> | $I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$                      |     | -0.85           | -1.2 | V    |
| Transition frequency  | $f_T$                | $V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$ |     | 200             |      | MHz  |
| Collector output capacitance<br>(Common base, input open circuited) | C <sub>ob</sub>      | $V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$               |     | 20              | 30   | pF   |

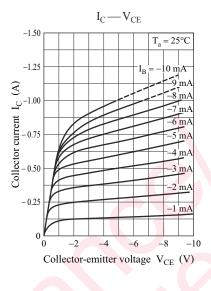
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

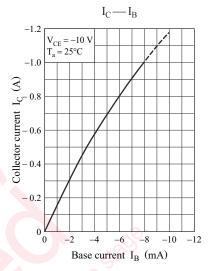
#### 2. \*: Rank classification

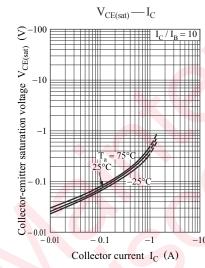
| Rank               | Q         | R          | S          |
|--------------------|-----------|------------|------------|
| $h_{\mathrm{FE1}}$ | 85 to 170 | 120 to 240 | 170 to 340 |

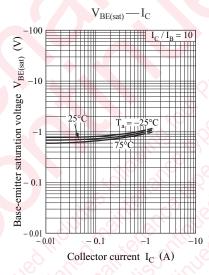
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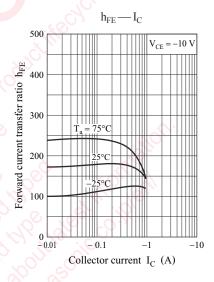


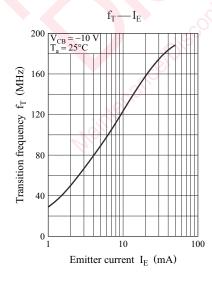


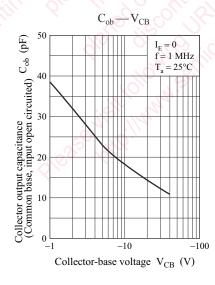


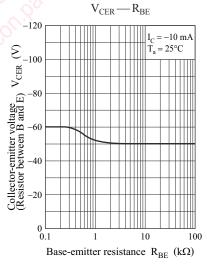






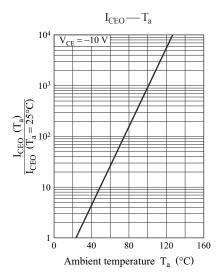


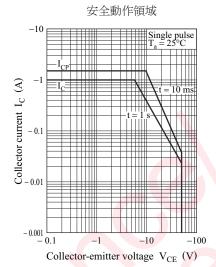




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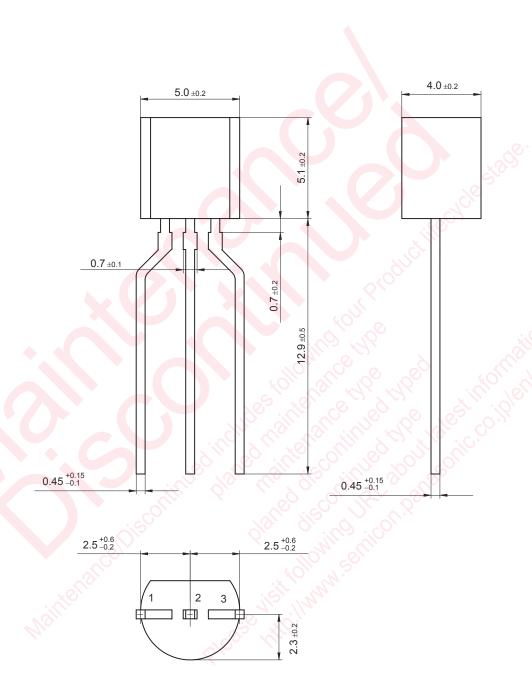




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TO-92-B1 Unit: mm



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